

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

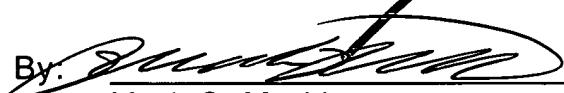
Patent Application Serial No. 10/041,896
Filing Date January 7, 2002
Inventor Brenda D. Kraus et al.
Assignee Micron Technology, Inc.
Group Art Unit 2813
Examiner Yennhu B. Huynh
Attorney Docket No. MI22-1859
Title: DRAM Circuitry Having Storage Capacitors Which Include Capacitor Dielectric Regions Comprising Aluminum Nitride

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

References -- See Attached Form PTO-1449

The attached form PTO-1449 is submitted in compliance with 37 CFR §1.56. Copies of the cited art are included. No admission is made regarding whether all the submitted references are prior art.

Respectfully submitted,

Dated: 5-29-03By: Mark S. Matkin
Reg. No. 32,268

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